MBR6045PT

SWITCHMODE™ Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 60 A Total (30 A Per Diode Leg)
- Pb−Free Packages are Available*

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

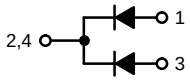
Mechanical Characteristics

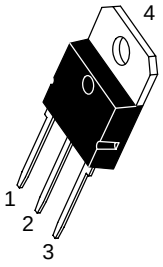
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B
  Machine Model C

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

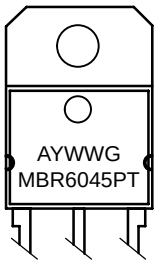
SCHOTTKY BARRIER RECTIFIER 60 AMPERES 45 VOLTS





SOT−93
CASE 340D
STYLE 2

MARKING DIAGRAM



MBR6045PT	= Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
G	= Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
MBR6045PT	SOT−93	30 Units/Rail
MBR6045PTG	SOT−93 (Pb−Free)	30 Units/Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R, T_C = 125°C) Per Diode Per Device	$I_{F(AV)}$	 30 60	A
Peak Repetitive Forward Current, (Rated V_R, Square Wave, 20 kHz @ T_C = 90°C) Per Diode	I_{FRM}	60	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	500	A
Peak Repetitive Reverse Current (2.0 μs, 1.0 kHz)	I_{RRM}	2.0	A
Storage Temperature Range	T_{stg}	−65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	−65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	°C
Voltage Rate of Change	dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction−to−Case	Min. Pad	$R_{\theta JC}$	1.0	°C/W
Maximum Thermal Resistance, Junction−to−Ambient	Min. Pad	$R_{\theta JA}$	60	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2) (i_F = 30 Amps, T_j = 25°C) (i_F = 30 Amps, Tj = 125°C) (i_F = 60 Amps, Tj = 25°C)	v_F	 − − −	 0.55 0.51 0.70	 0.62 0.55 0.75	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, Tj = 25°C) (Rated dc Voltage, Tj = 125°C)	i_R	 − −	 0.2 35	 1.0 50	mA

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

TYPICAL ELECTRICAL CHARACTERISTICS

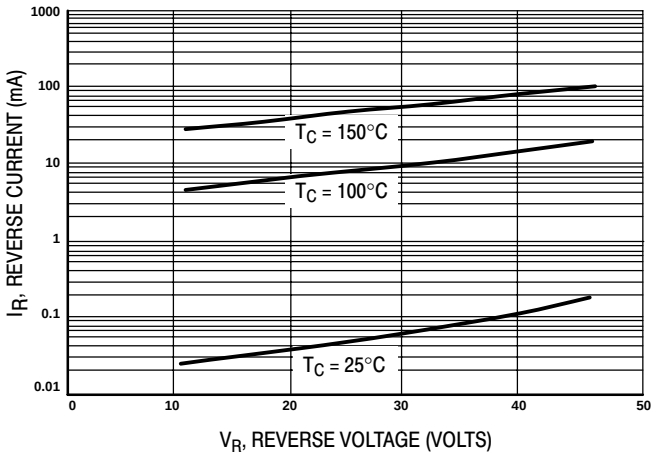


Figure 1. Typical Reverse Current

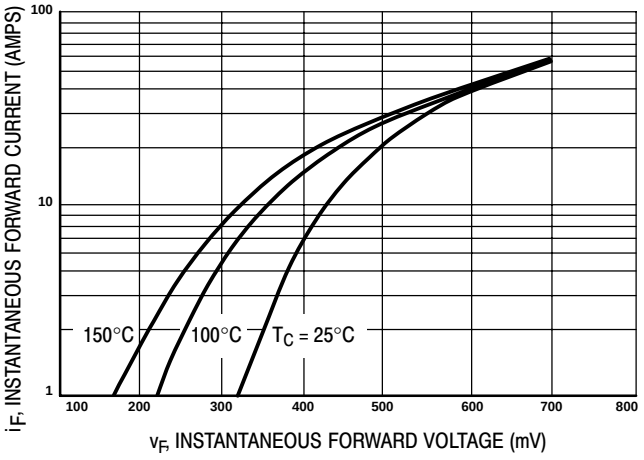
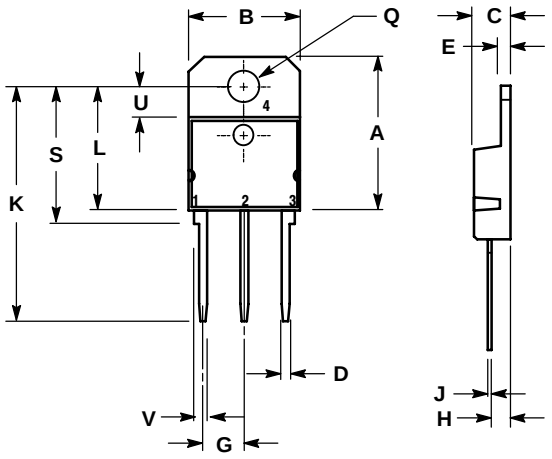


Figure 2. Typical Forward Voltage

PACKAGE DIMENSIONS

SOT−93
(TO−218)
CASE 340D−02
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

STYLE 2:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE